

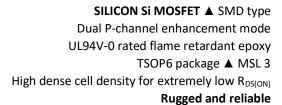




-20V ▲ 65mΩ ▲ -3.3A ▲ Dual Si MOSFET









MAXIMUM RATINGS

Parameter (T _A = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	-20V
Gate-Source Voltage	V _{GS}	±12V
Continuous Drain Current	I _D	-3.3A
Pulsed Drain Current Note 1	I _{DM}	-13.2A
Maximum Power Dissipation	P _D	1.14W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

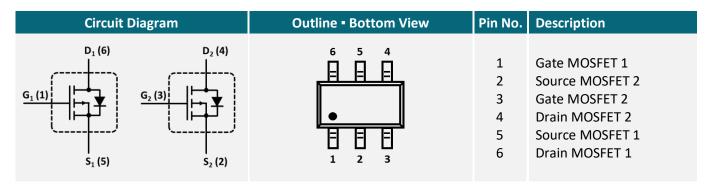
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	110°C/W

APPLICATIONS

Data Server	DC/DC	Network	Portable	USB
Control	Converter	Devices	Products	Storage
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PIN DESCRIPTION





ELECTRICAL CHARACTERISTICS ▲ T_A = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = -250\mu A$	BV _{DSS}	-20			V
Zero Gate Voltage Drain Current	V_{DS} = -20V, V_{GS} = 0V	I _{DSS}			-1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 12V, V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -12V, V_{DS} = 0V$	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250 \mu A$	$V_{GS(th)}$	-0.4		-1	V
Static Drain-Source On-Resistance	$V_{GS} = -4.5V$, $I_{D} = -3A$	R _{DS(ON)}		60	65	mΩ
Static Drain-Source On-Resistance	$V_{GS} = -2.5V$, $I_{D} = -2A$	R _{DS(ON)}		80	100	mΩ
Static Drain-Source On-Resistance	$V_{GS} = -1.8V$, $I_{D} = -1A$	R _{DS(ON)}		110	150	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		405		pF
Output Capacitance	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		70		pF
Reverse Transfer Capacitance	V_{DS} = -15V, V_{GS} = 0V, f = 1MHz C_{RSS}			55		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = -15V, V_{GS} = -4.5V, I_D = -3A, $R_{G(ext)}$ = 6Ω	t _{D(ON)}		15		ns
Turn-On Rise Time	V_{DD} = -15V, V_{GS} = -4.5V, I_D = -3A, $R_{G(ext)}$ = 6Ω	t _R		8		ns
Turn-Off Delay Time	V_{DD} = -15V, V_{GS} = -4.5V, I_D = -3A, $R_{G(ext)}$ = 6Ω	$t_{D(OFF)}$		47		ns
Turn-Off Fall Time	V_{DD} = -15V, V_{GS} = -4.5V, I_D = -3A, $R_{G(ext)}$ = 6Ω	t _F		15		ns
Total Gate Charge	$V_{DD} = -15V$, $V_{GS} = -4.5V$, $I_{D} = -3A$	Q_{G}		5.7		nC
Gate Source Charge	$V_{DD} = -15V$, $V_{GS} = -4.5V$, $I_{D} = -3A$	Q_{GS}		0.5		nC
Gate Drain Charge	$V_{DD} = -15V$, $V_{GS} = -4.5V$, $I_{D} = -3A$	Q_{GD}		1.8		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		I _S			-0.95	Α
Drain-Source Diode Forward Voltage Note 3	$V_{GS} = 0V$, $I_S = -8A$	V_{SD}			-1.2	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, $t \le 5$ sec.
- 3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production testing.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



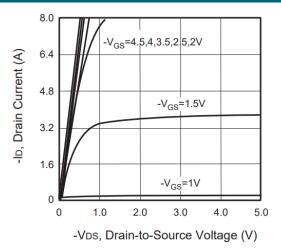


Fig. 2 • Transfer Characteristics

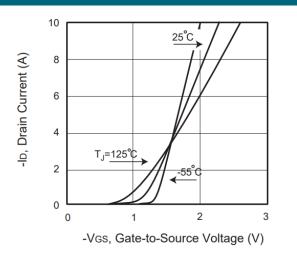


Fig. 3 • Capacitance

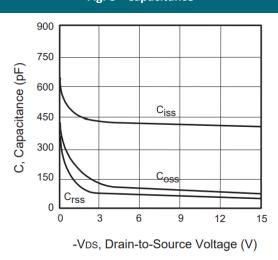


Fig. 4 • On-Resistance Variation with Temperature

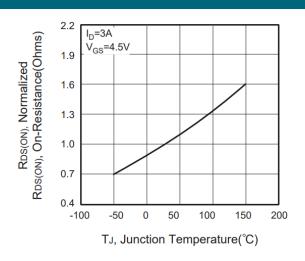


Fig. 5 • Gate Threshold Variation with Temperature

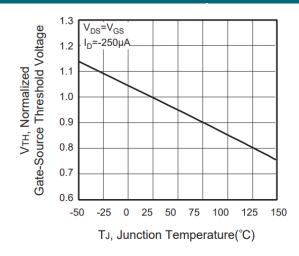
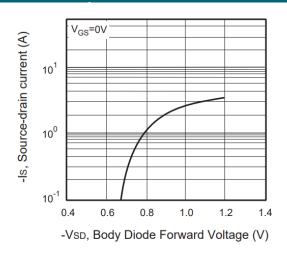


Fig. 6 • Body Diode Forward Voltage Variation with Source Current



MGT ▲ Manufacturer Group of Technology



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

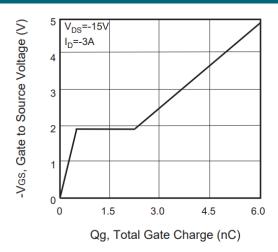


Fig. 8 • Maximum Safe Operating Area

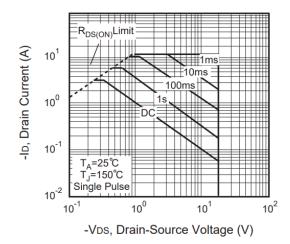


Fig. 9 • Breakdown Voltage Variation vs. Temperature

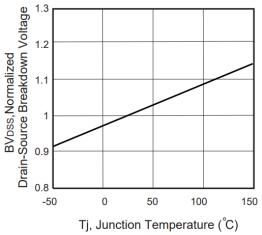
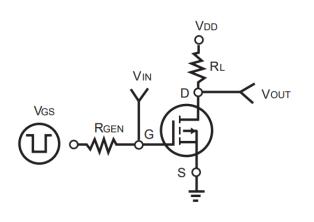
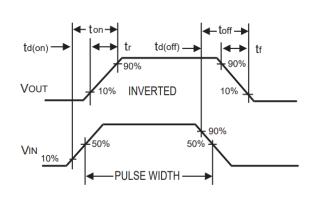


Fig. 10 • Switching Test Circuit Fig. 11 • Switching Waveforms

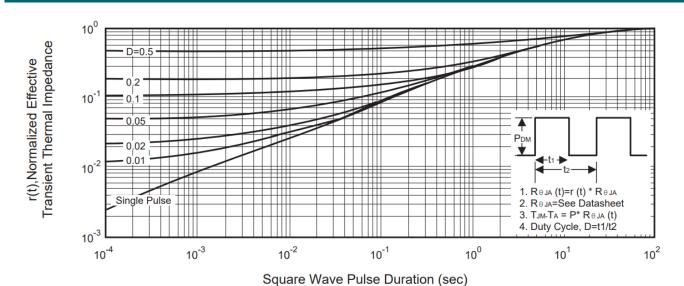




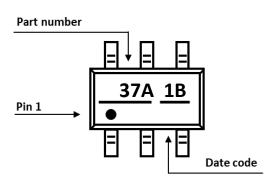


REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve

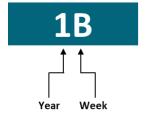


PART MARKING

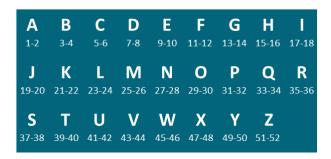


DATE CODE

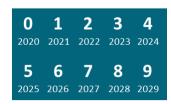
Example: 1B



Coding list for "Week"

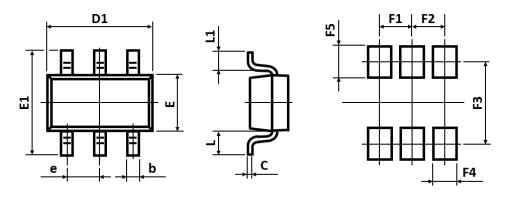


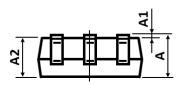
Coding list for "Year"





PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT





Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	0.800	-	1.250
A1	0.000	-	0.130
A2	0.700	-	1.200
b	0.300	-	0.500
С	0.090	-	0.200
D1	2.800	_	3.100

Sym	Millimeters Millimeters (Min.) (Typ.)		Millimeters (Max.)
E	1.500	-	1.700
E1	2.500	-	3.100
e		0.950 (TYP)	
L	0.350	-	0.800
L1	0.300	-	0.550

Sym	Millimeters (Min.)	Millimeters Millimeters (Min.) (Typ.)	
F1	-	0.950	-
F2	-	0.950	-
F3	-	2.600	-

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F4	-	0.700	-
F5	-	1.000	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

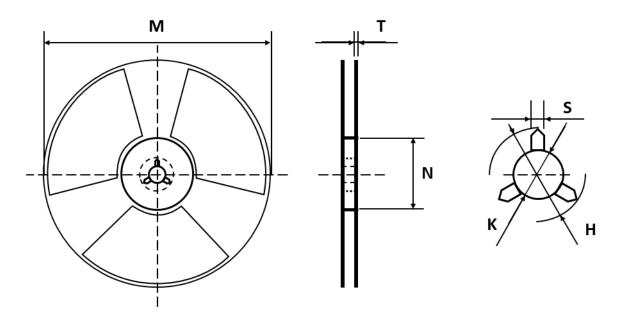
2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.
CEH2637A	TSOP 6	Reel	3,000pcs	15,000pcs

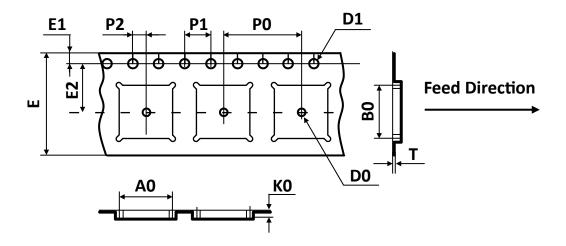


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	H	K	S
Q _{mam}	Ø180	Ø178.00	Ø54.00	1.20	20.00	13.30	3.00
8mm	M190	±1.00	±0.50	±0.20	±1.00	±0.30	±1.00

TAPE DIMENSIONS ▲ All dimensions in mm

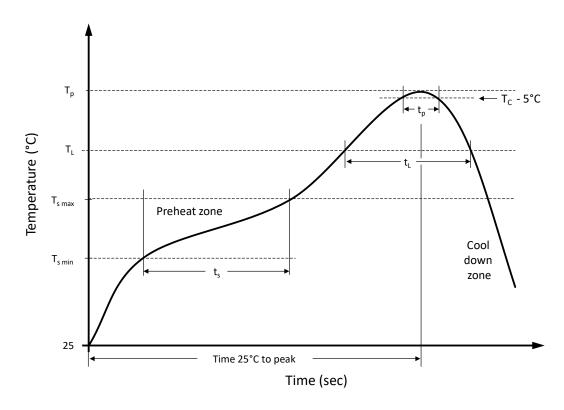


Pacl	kage	Α0	В0	КО	D0	D1	E	E1	E2	P0	P1	P2	Т
TC	OP6	3.20	3.20	1.35	1.00	1.50	8.00	1.75	3.50	4.00	4.00	2.00	0.20
130	UPG	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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